

P-Channel 150 V (D-S) MOSFET

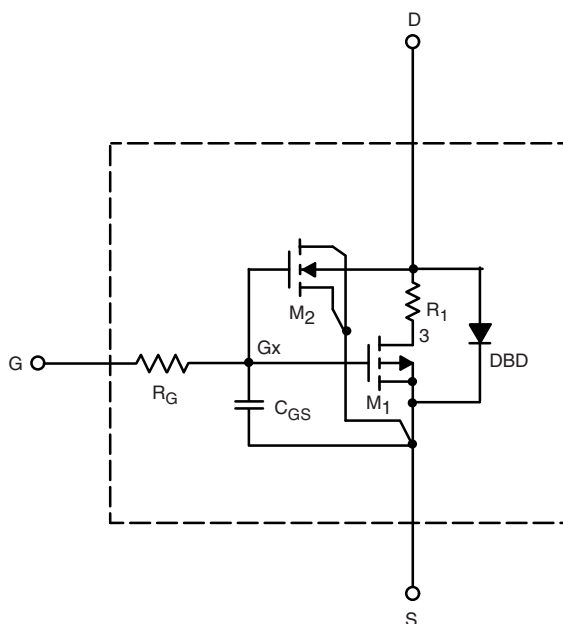
DESCRIPTION

The attached SPICE model describes the typical electrical characteristics of the p-channel vertical DMOS. The subcircuit model is extracted and optimized over the - 55 °C to + 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage. A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

CHARACTERISTICS

- P-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the - 55 °C to + 125 °C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

SUBCIRCUIT MODEL SCHEMATIC



Note

- This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

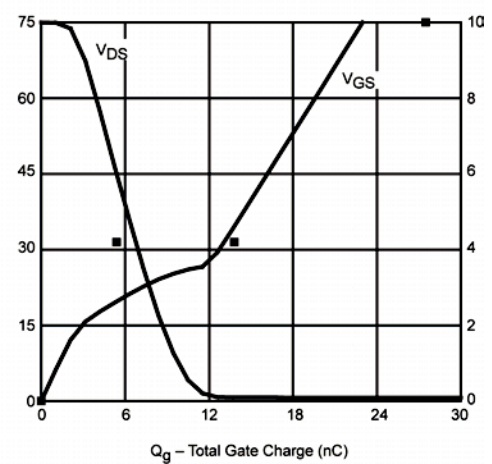
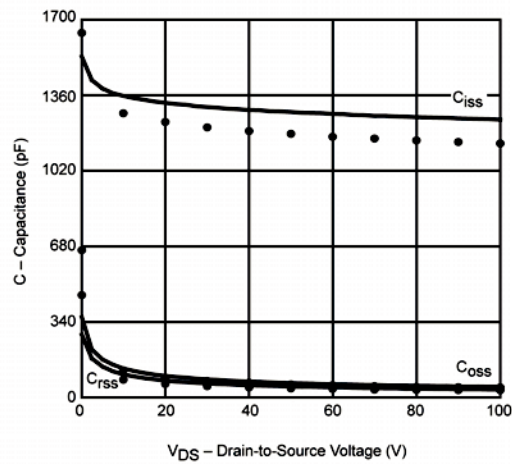
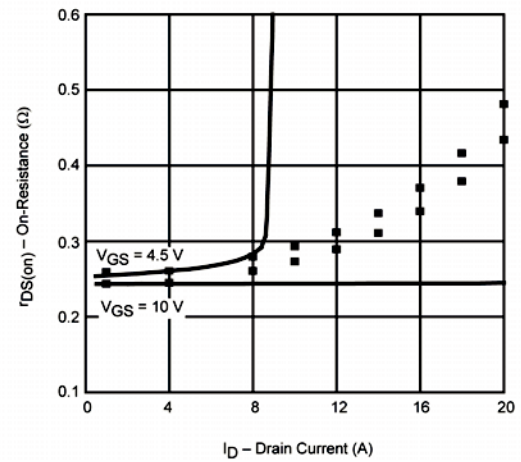
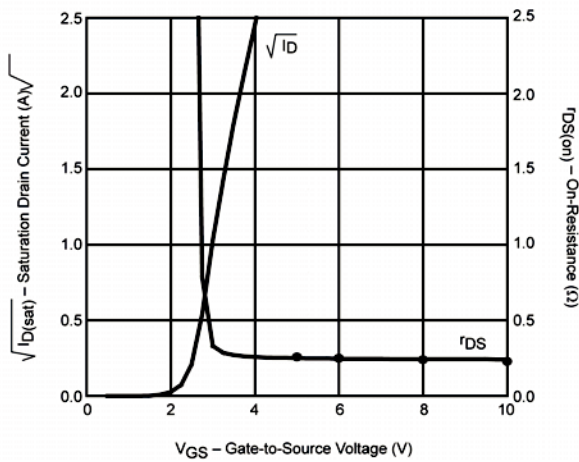
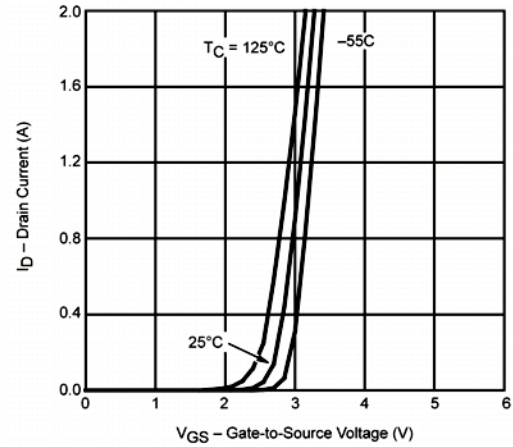
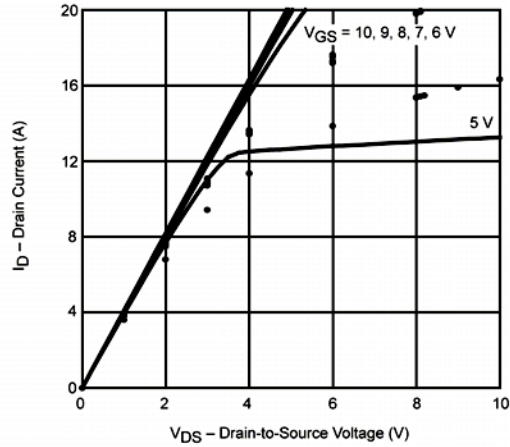
**SPECIFICATIONS** ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\text{ }\mu\text{A}$	2	-	V
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\text{ V}$, $V_{GS} = -10\text{ V}$	41	-	A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}$, $I_D = -4\text{ A}$	0.244	0.245	Ω
		$V_{GS} = -4.5\text{ V}$, $I_D = -3\text{ A}$	0.258	0.260	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15\text{ V}$, $I_D = -4\text{ A}$	6	12	S
Diode Forward Voltage ^a	V_{SD}	$I_S = -3\text{ A}$, $V_{GS} = 0\text{ V}$	-0.82	-0.80	V
Dynamic^b					
Input Capacitance	C_{iss}	$V_{DS} = -50\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$	1285	1190	pF
Output Capacitance	C_{oss}		65	61	
Reverse Transfer Capacitance	C_{rss}		50	42	
Total Gate Charge	Q_g	$V_{DS} = -75\text{ V}$, $V_{GS} = -10\text{ V}$, $I_D = -3\text{ A}$	23	27.5	nC
		$V_{DS} = -75\text{ V}$, $V_{GS} = -6\text{ V}$, $I_D = -3\text{ A}$	16	23.2	
Gate-Source Charge	Q_{gs}		5.4	5.4	
Gate-Drain Charge	Q_{gd}		8.4	8.4	

Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

COMPARISON OF MODEL WITH MEASURED DATA ($T_J = 25^\circ\text{C}$, unless otherwise noted)



Note

- Dots and squares represent measured data.